

AMENDMENTS TO THE SPECIFICATION

At page 8, please replace paragraph 3 starting at line 8 with the following paragraph:

“To read information from the memory cells 101, a voltage or electric field (*e.g.*, 2 volts, 1 volts, 0.5 volts) can be applied *via* the controller 102 ~~12~~. Subsequently, an impedance measurement can be performed which, therein determines which operating state one or more of the memory cells are in (*e.g.*, high impedance, very low impedance, low impedance, medium impedance, and the like). As stated *supra*, the impedance relates to, for example, “on” (*e.g.*, 1) or “off” (*e.g.*, 0) for a dual state device, or to “00”, “01”, “10”, or “11” for a quad state device. It is appreciated that other numbers of states can provide other binary interpretations. To erase information written into the memory cells 101, a negative voltage or a polarity opposite the polarity of the writing signal that exceeds a threshold value can be applied.